

COS/MOS INTEGRATED CIRCUIT



HCC/HCF 40105B

7929225 S G S SEMICONDUCTOR CORP

FIFO REGISTER

- INDEPENDENT ASYNCHRONOUS INPUTS AND OUTPUTS
- 3-STATE OUTPUTS
- EXPANDABLE IN EITHER DIRECTION
- STATUS INDICATORS ON INPUT AND OUTPUT
- RESET CAPABILITY
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

The **HCC 40105B** (extended temperature range) and **HCF 40105B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and ceramic flat package.

The **HCC/HCF 40105B** is a low-power first-in-first-out (FIFO) "elastic" storage register that can store 16 4-bit words. It is capable of handling input and output data at different shifting rates. This feature makes it particularly useful as a buffer between asynchronous systems. Each word position in the register is clocked by a control flip-flop, which stores a marker bit. A "1" signifies that the position's data is filled and a "0" denotes a vacancy in that position. The control flip-flop detects the state of the preceding flip-flop and communicates its own status to the succeeding flip-flop. When a control flip-flop is in the "0" state and sees a "1" in the preceding flip-flop, it generates a clock pulse that transfers data from the preceding four data latches into its own four data latches and resets the preceding flip-flop to "0". The first and last control flip-flops have buffered outputs. Since all empty locations "bubble" automatically to the input end, and all valid data ripple through to the output end, the status of the first control flip-flop (DATA-IN READY) indicates if the FIFO is full, and the status of the last flip-flop (DATA-OUT READY) indicates if the FIFO contains data. As the earliest data are removed from the bottom of the data stack (the output end), all data entered later will automatically propagate (ripple) toward the output.

ABSOLUTE MAXIMUM RATINGS

V_{DD}^*	Supply voltage: HCC types	-0.5 to 20	V
	HCF types	-0.5 to 18	V
V_I	Input voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC input current (any one input)	± 10	mA
P_{tot}	Total power dissipation (per package)	200	mW
	Dissipation per output transistor		
	for T_{op} = full package-temperature range	100	mW
T_{op}	Operating temperature: HCC types	-55 to 125	°C
	HCF types	-40 to 85	°C
T_{stg}	Storage temperature	-65 to 150	°C

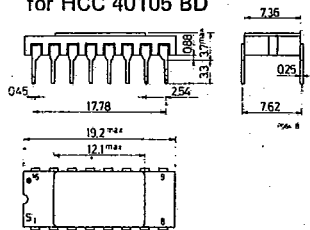
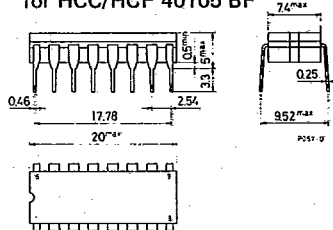
* All voltage values are referred to V_{SS} pin voltage

ORDERING NUMBERS:

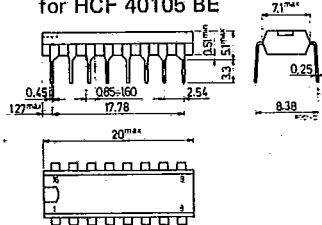
HCC 40105 BD for dual in-line ceramic package
 HCC 40105 BF for dual in-line ceramic package, frit seal
 HCC 40105 BK for ceramic flat package
 HCF 40105 BE for dual in-line plastic package
 HCF 40105 BF for dual in-line ceramic package, frit seal

7929225 S G S SEMICONDUCTOR CORP

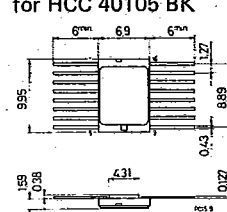
MECHANICAL DATA (dimensions in mm)

Dual in-line ceramic package
for HCC 40105 BD 735Dual in-line ceramic package
for HCC/HCF 40105 BF 7400

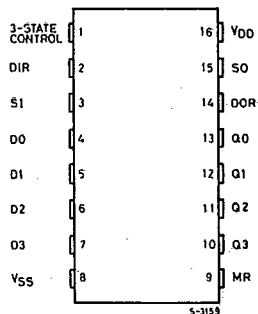
Dual in-line plastic package
for HCF 40105 BE Z1™



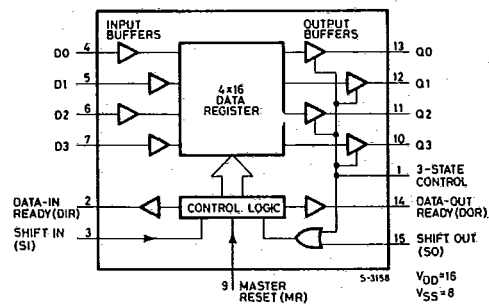
**Ceramic flat package
for HCC 40105 BK**



PIN CONNECTIONS



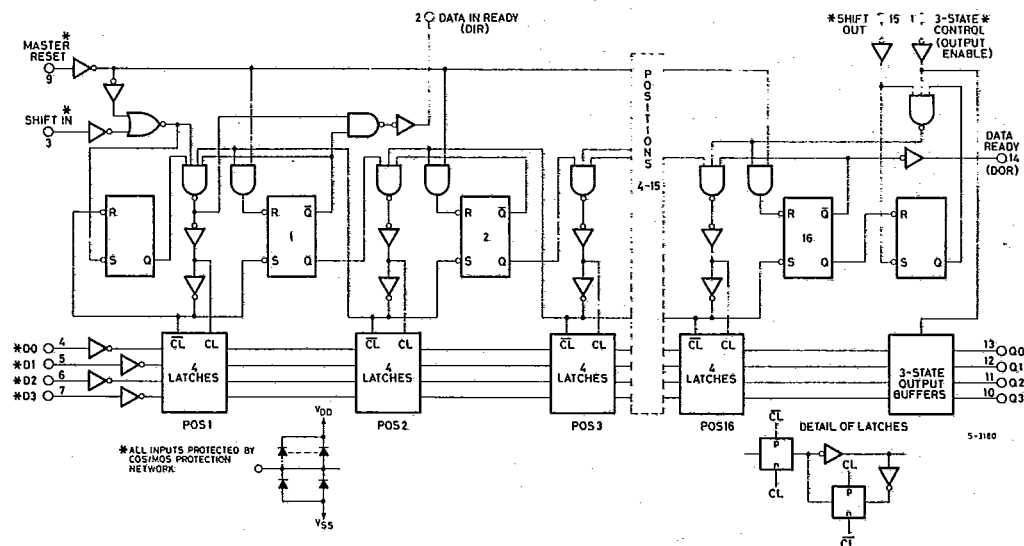
FUNCTION DIAGRAM



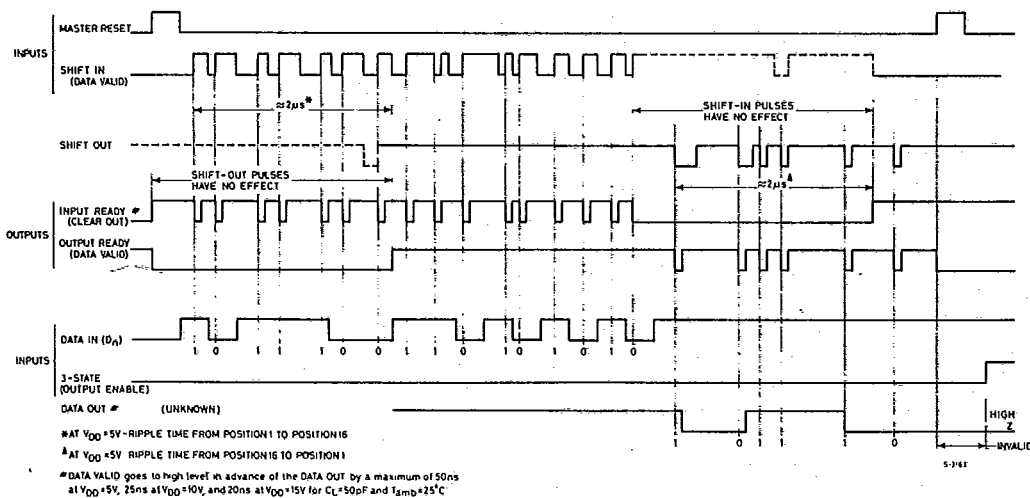
RECOMMENDED OPERATING CONDITIONS

V _{DD}	Supply voltage: HCC types	3 to 18	V
	HCF types	3 to 15	V
V _I	Input voltage	0 to V _{DD}	V
T _{op}	Operating temperature: HCC types	-55 to 125	°C
	HCF types	-40 to 85	°C

LOGIC DIAGRAM

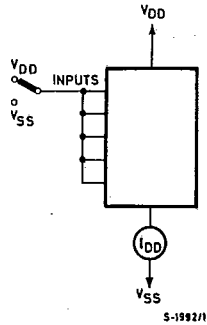


TIMING DIAGRAM

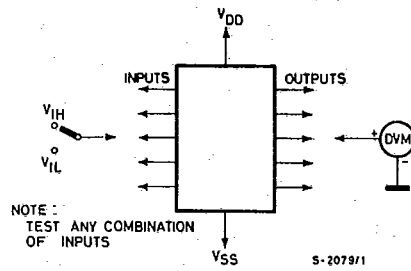


TEST CIRCUITS

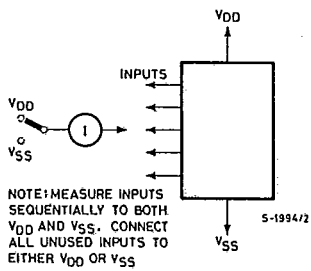
Quiescent device current



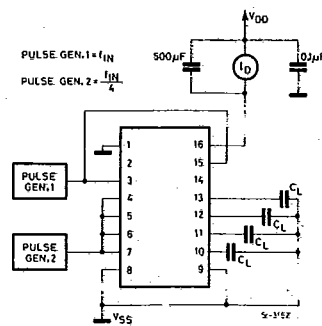
Input voltage



Input leakage current

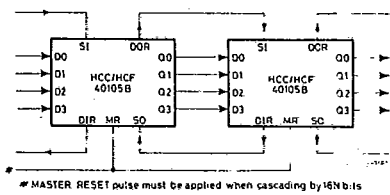


Dynamic power dissipation

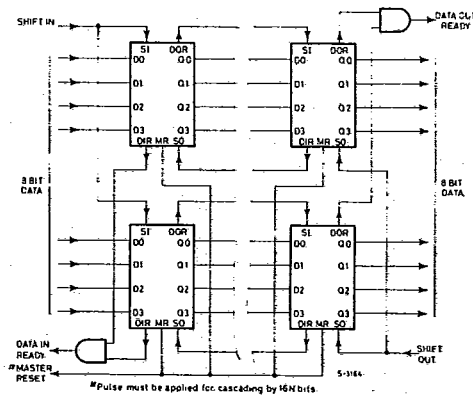


TYPICAL APPLICATIONS

Expansion, 4 bits-wide-by-16 N-bits long



Expansion, 8 bits-wide-by-16 N-bits long





HCC/HCF 40105B

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Parameter			Test conditions				Values						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent current	HCC types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
		HCF types	0/20			20		100		0.08	100		3000	
			0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15			15		80		0.04	80		600				
V _{OH}	Output high voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output low voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input high voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input low voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output drive current	HCC types	0/ 5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/ 5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
		HCF types	0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
			0/ 5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/ 5	4.6		5	-0.52		-0.44	-1		-0.36		
I _{OL}	Output sink current	HCC types	0/10	9.5		10	-1.3		-1.1	-2.6		-0.9	mA	
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
			0/ 5	0.4		5	0.64		0.51	1		0.36		
		HCF types	0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
			0/ 5	0.4		5	0.52		0.44	1		0.36		
I _{IH} , I _{IL}	Input leakage current	HCC types	0/18	Any input		18		±0.1		±10 ⁻⁵	±0.1		± 1	μA
		HCF types	0/15			15		±0.3		±10 ⁻⁵	±0.3		± 1	
I _{OH} , I _{OL} **	3-state output leakage current	HCC types	0/18	0/18		18		±0.4		±10 ⁻⁴	±0.4		±12	μA
		HCF types	0/15	0/15		15		±1.0		±10 ⁻⁴	±1.0		±7.5	
C _I	Input capacitance			Any input					5	7.5			pF	

* T_{Low} = - 55°C for HCC device; -40°C for HCF device.

* T_{High} = +125°C for HCC device; +85°C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}= 5V

2V min. with V_{DD}= 10V

** Forced output disable. 2.5V min. with V_{DD}= 15V

HCC/HCF 40105B

41C 09107 DT-46-35

7929225 S G S SEMICONDUCTOR CORP

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20 ns)

Parameter	Test conditions	Values			Unit
		V_{DD} (V)	Min.	Typ.	Max.
t_{PHL} Propagation delay time Shift-Out or Reset to Data-Out Ready		5		185	370
		10		90	180
		15		65	130
t_{PHL} Propagation delay time Shift-In to Data-In Ready		5		160	320
		10		65	130
		15		45	90
t_{pZH} , t_{pZL} Propagation delay time 3-State Control to Data-Out		5		140	280
		10		60	120
		15		40	80
t_{pHZ} , t_{pLZ} Propagation delay time 3-State Control to Data-Out		5		100	200
		10		50	100
		15		40	80
t_{PLH} Ripple-Through Delay Input to Output		5		2	4
		10		1	2
		15		0.7	1.4
t_{THL} t_{TLH} Transition time		5		100	200
		10		50	100
		15		40	80
f_I Shift-In or Shift-Out Rate		5		1.5	3
		10		3	6
		15		4	8
t_{WH} Shift-In pulse width		5	200	100	
		10	80	40	
		15	60	30	
t_{WL} Shift-Out pulse width		5	360	180	
		10	160	80	
		15	100	50	
t_r Shift-In or Shift-Out Rise time		5			15
		10			15
		15			15
t_f Shift-In fall time		5			15
		10			15
		15			15
t_f Shift-Out fall time		5			15
		10			5
		15			5
t_{setup} Data setup time		5	0		
		10	0		
		15	0		
t_{hold} Data hold time		5	350	175	
		10	150	75	
		15	120	60	



41C 09108 DT-46-35

DINAMIC ELECTRICAL CHARACTERISTICS (continued)

Parameter	Test conditions	Values			Unit
		V _{DD} (V)	Min.	Typ.	Max.
t _{WL} Data-In Ready pulse width		5		260	520
		10		100	200
		15		70	140
t _{WL} Data-Out Ready pulse width		5		220	440
		10		90	180
		15		65	130
t _{WH} Master Reset pulse width		5	200	100	
		10	90	45	
		15	60	30	

APPLICATIONS INFORMATION

Loading Data — Data can be entered whenever the DATA-IN READY (DIR) flag is high, by a low to high transition on the SHIFT-IN (SI) input. This input must go low momentarily before the next word is accepted by the FIFO. The DIR flag will go low momentarily, until the data have been transferred to the second location. The flag will remain low when all 16-word locations are filled with valid data, and further pulses on the SI input will be ignored until DIR goes high.

Unloading Data — As soon as the first word has rippled to the output, DATA-OUT READY (DOR) goes high, and data can be removed by a falling edge on the SO input. This falling edge causes the DOR signal to go low while the word on the output is dumped and the next word moves to the output. As long as valid data are available in the FIFO, the DOR signal will go high again signifying that the next word is ready at the output. When the FIFO is empty, DOR will remain low, and any further commands will be ignored until a "1" marker ripples down to the last control register, when DOR goes high. Unloading of data is inhibited while the 3-state control input is high. The 3-state control signal should not be shifted from high to low (data outputs turned on) while the SHIFT-OUT is at logic 0. This level change would cause the first word to be shifted out (unloaded) immediately and the data to be lost.

Cascading — The HCC/HCF 40105B can be cascaded to form longer registers simply by connecting the DIR to SO and DOR to SI. In the cascaded mode, a MASTER RESET pulse must be applied after the supply voltage is turned on. For words wider than 4 bits, the DIR and the DOR outputs must be gated together with AND gates. Their outputs drive the SI and SO inputs in parallel, if expanding is done in both directions.

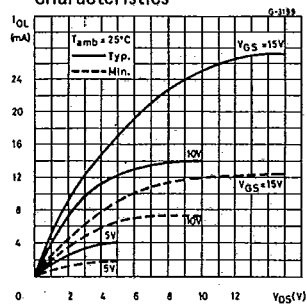
3-State Outputs — In order to facilitate data busing, 3-state outputs are provided on the data output lines, while the load condition of the register can be detected by the state of the DOR output.

Master Reset — A high on the MASTER RESET (MR) sets all the control logic marker bits to "0". DOR goes low and DIR goes high. The contents of the data register are not changed, only declared invalid, and will be superseded when the first word is loaded.

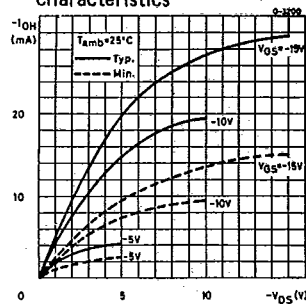
HCC/HCF 40105B

41C 09109 DT-46-35

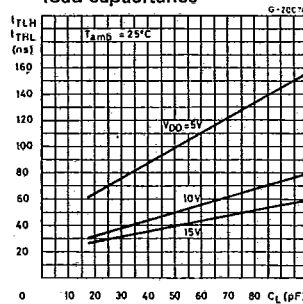
Output low (sink) current characteristics



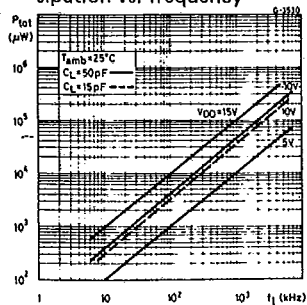
Output high (source) current characteristics

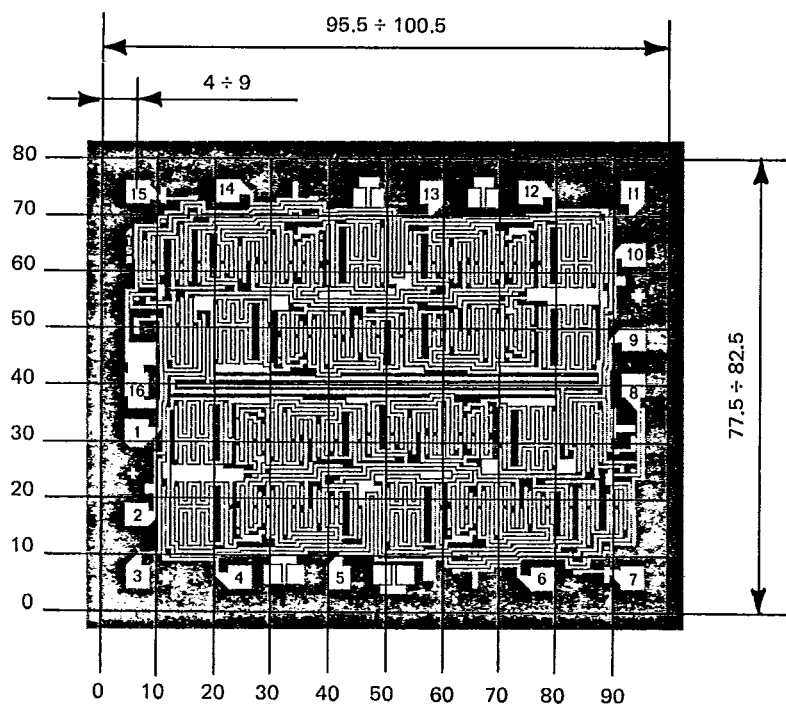


Typical transition time vs. load capacitance

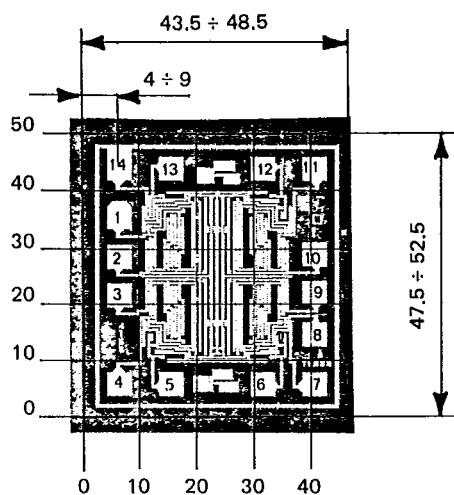


Typical dynamic power dissipation vs. frequency





4015B



4016B